AccessionIndex: TCD-SCSS-V.20221220.005
Accession Date: 20-Dec-2022
Accession By: Dr.Brian Coghlan
Object name: PNMOS Type 25120 Write Only Memory
Vintage: 1984
Synopsis: Spoof 9046 x N-bit WOM chip datasheet.

Description:
This April Fool's spoof datasheet is a derivative of earlier examples, "revised in April 1984", with a number of changes, e.g. "extremely low power consumption providing the chip is properly cooled" (which actually might be so for superconducting devices). The classic write-only memory spoof was published in 1972 as a joke pseudo-product in the Signetics semiconductor catalog, the Signetics 25120 Series 9C46XN [1][2][3].

Many thanks to Brian Coghlan for donating this item.

The homepage for this catalog is at: https://www.scss.tcd.ie/SCSSTreasuresCatalog/
Click *'Accession Index'* (1st column listed) for related folder, or *'About'* for further guidance. Some of the items below may be more properly part of other categories of this catalog, but are listed here for convenience.

Accession Index	Object with Identification
TCD-SCSS-V.20221220.005	PNMOS Type 25120 Write Only Memory, Spoof 9046 x N-bit WOM chip datasheet, 1984.

References:

1. Wikipedia, *Write-only memory (joke)*, see:
https://en.wikipedia.org/wiki/Write-only_memory_(joke)
Last browsed to on 20-Dec-2022.

2. John G. Curtis, *Fully Encoded, 9046 X N, Random Access Write-Only-Memory*, Signetics, 1972, see:
https://www.scss.tcd.ie/SCSSTreasuresCatalog/literature/TCD-SCSS-V.20221220.005/Signetics-25120-9046xN-WriteOnlyMemory-JohnGCurtis-1972.pdf
Last browsed to on 20-Dec-2022.

3. Signetics, *Fully Encoded, 9046 X N, Random Access Write-Only-Memory*, see:
https://www.scss.tcd.ie/SCSSTreasuresCatalog/literature/TCD-SCSS-V.20221220.005/Signetics-25120-9046xN-WriteOnlyMemory-cleanPDF.pdf
Last browsed to on 20-Dec-2022.

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K259 / 3609.

DATA SHEET

PNMOS
LSI

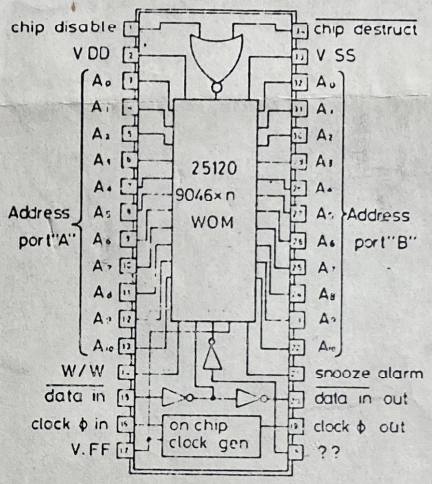
TYPE 25120
9046×n BIT RANDOM ACCESS WRITE ONLY MEMORY
revised april 1984

applications:

- least significant control memories
- post mortem memories
  (weapon guidance systems)
- artificial memory systems
- non-intelligent micro controllers
- first-in never-out (FINO)
  asynchronus buffers
- overflow register (bit bucket)

features:

- fully encoded multi-port addressing
- write cycle time 79ns (max typ)
- read access time[1]
- cell refresh time 2ms (min typ).
- TTL/DTL compatible inputs
- clock input capacitance 2pF max[2]
- VDD = 0v ± 3%, VCC=10v, VFF=6,3v AC.



description:

The 25120 is a 9046×n bit random access write only memory Due to the employment of our proprietary Sanderson-Rabbet enhanced depetion mode which utilises both P&N channel MOS devices the 25120 is capable of 50% higher speeds than you will be able to obtain. A single TTL level clock phase is required to drive the internal clock generator. The static memory cells are operated dynamically to yield an extremely low power dissipation providing the chip is properly cooled This is easily done with a 6ft fan placed 1/2" from the package If the device fails you have exceeded the ratings, under these circumstances a larger fan is recommended All inputs and outputs are directly TTL compatible[3] providing the correct interfacing circuitry is employed. In any event use a 1A fuse in all supply and data lines

The use of the unique SEX[4] process allows phenomenal rates of production[5] thus ensuring the availability of this versatile device All terminals are provided with slip-on latex protectors for the prevention of Voltage Destruction (pill packaged devices do not require protection) The use of a low cost silicone DIP packaging ensures reliability by the use of non-hermetic sealing which prevents the capture of harmful ions while allowing the free exchange of friendly ions

Data refresh is accomplished during CB[6] and LH[6] periods.

notes -

1) not applicable
2) measured at 13MHz with 26mV into 19pF
3) we dont know how but you can take our word for it
4) Special EXtra secret
5) see modern production techniques by T Arrieta (not yet written)
6) coffee break and lunch hour.
7) typical of all inputs and outputs.

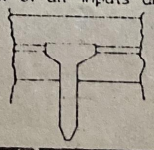


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Figure 1: PNMOS Type 25120 Write Only Memory datasheet

R259 / 9609.

DATA SHEET

PNMOS
LSI

TYPE 25120
9046×n BIT RANDOM ACCESS WRITE ONLY MEMORY
revised april 1984

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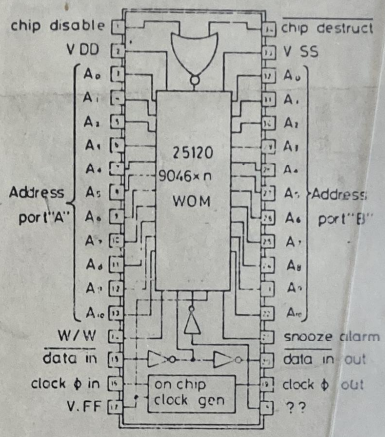

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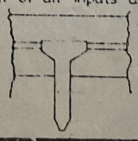

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Figure 2: PNMOS Type 25120 Write Only Memory datasheet in protective cover